CY7C161
CY7C162

16K x 4 Static RAM with Separate I/O

Features

- **High speed**
  - **15-ns**
- **Transparent write (7C161)**
- **CMOS for optimum speed/power**
- **Low active power**
  - **633 mW**
- **Low standby power**
  - **220 mW**
- **TTL compatible inputs and outputs**
- **Automatic power-down when deselected**

Functional Description

The CY7C161 and CY7C162 are high-performance CMOS static RAMs organized as 16,384 by 4 bits with separate I/O. Easy memory expansion is provided by active LOW chip enables ($\overline{CE}_1$, $\overline{CE}_2$) and three-state drivers. They have an automatic power-down feature, reducing the power consumption by 65% when deselected.

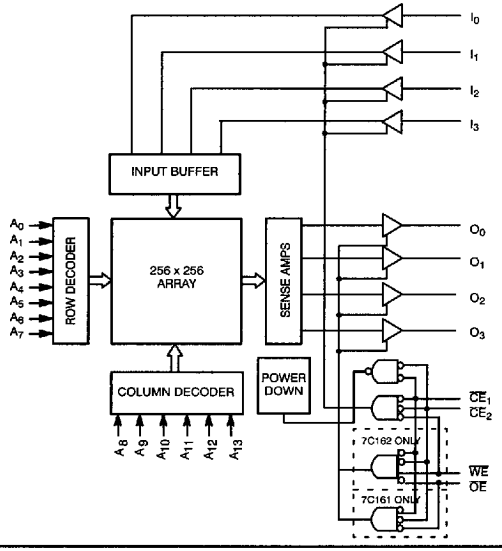
Writing to the device is accomplished when the chip enable ($\overline{CE}_1$, $\overline{CE}_2$) and write enable ($\overline{WE}$) inputs are both LOW. Data on the four input pins (I_0 through I_3) is written into the memory location specified on the address pins (A_0 through A_{13}).

Reading the device is accomplished by taking the chip enables ($\overline{CE}_1$, $\overline{CE}_2$) LOW while write enable ($\overline{WE}$) remains HIGH. Under these conditions the contents of the memory location specified on the address pins will appear on the four data output pins.

The output pins stay in a high-impedance state when write enable ($\overline{WE}$) is LOW (7C162 only), or one of the chip enables ($\overline{CE}_1$, $\overline{CE}_2$) are HIGH.

A die coat is used to ensure alpha immunity.

Logic Block Diagram



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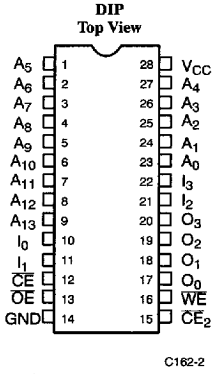
Pin Configurations



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Selection Guide[1]

	7C161–12 7C162–12	7C161–15 7C162–15	7C161–20 7C162–20	7C161–25 7C162–25	7C161–35 7C162–35
Maximum Access Time (ns)	12	15	20	25	35
Maximum Operating Current (mA)	160	115	80	70	70
Maximum Standby Current (mA)	40/20	40/20	40/20	20/20	20/20

Shaded areas indicate preliminary information.

Note:
1. For military specifications, see the CY7C161A/CY7C162A datasheet.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... −65°C to +150°C

Ambient Temperature with Power Applied ..... −55°C to +125°C

Supply Voltage to Ground Potential (Pin 24 to Pin 12) ..... −0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State[2] ..... −0.5V to +7.0V

DC Input Voltage[2] ..... −0.5V to +7.0V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current ..... >200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	5V ± 10%

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Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	7C161−12 7C162−12		7C161−15 7C162−15		Unit
			Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −4.0 mA	2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage[2]		−0.5	0.8	−0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}	−5	+5	−5	+5	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled	−5	+5	−5	+5	µA
I_{OS}	Output Short Circuit Current[3]	V_{CC} = Max., V_{OUT} = GND		−350		−350	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA		160		115	mA
I_{SB1}	Automatic $\overline{CE}_1$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{IH} Min. Duty Cycle = 100%		40		40	mA
I_{SB2}	Automatic $\overline{CE}_1$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{CC} − 0.3V, V_{IN} ≥ V_{CC} − 0.3V or V_{IN} ≤ 0.3V		20		20	mA

Shaded areas indicate preliminary information.

Electrical Characteristics Over the Operating Range (continued)

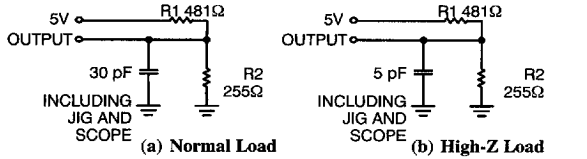
Parameter	Description	Test Conditions	7C161–20 7C162–20		7C161–25 ,35 7C162–25 ,35		Unit
			Min.	Max.	Min.	Max.	
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = −4.0 mA	2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA		0.4		0.4	V
V_{IH}	Input HIGH Voltage		2.2	V_{CC}	2.2	V_{CC}	V
V_{IL}	Input LOW Voltage[2]		−0.5	0.8	−0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}	−5	+5	−5	+5	μA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{CC}, Output Disabled	−5	+5	−5	+5	μA
I_{OS}	Output Short Circuit Current[3]	V_{CC} = Max., V_{OUT} = GND		−350		−350	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., I_{OUT} = 0 mA		80		70	mA
I_{SB1}	Automatic $\overline{CE}_1$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{IH} Min. Duty Cycle = 100%		40		20	mA
I_{SB2}	Automatic $\overline{CE}_1$ Power-Down Current	Max. V_{CC}, $\overline{CE}_1$ ≥ V_{CC} − 0.3V, V_{IN} ≥ V_{CC} − 0.3V or V_{IN} ≤ 0.3V		20		20	mA

Capacitance[4]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	10	pF
C_{OUT}	Output Capacitance		10	pF

Notes:
2. Minimum voltage is equal to −3.0V for pulse durations less than 30 ns.
3. Not more than 1 output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
4. Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms



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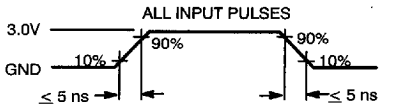

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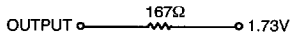
Equivalent to: THÉVENIN EQUIVALENT



Switching Characteristics Over the Operating Range[5, 6]

Parameter	Description	7C161–12 7C162–12		7C161–15 7C162–15		7C161–20 7C162–20		7C161–25 7C162–25		7C161–35 7C162–35		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
READ CYCLE												
t_{RC}	Read Cycle Time	12		15		20		25		35		ns
t_{AA}	Address to Data Valid		12		15		20		25		35	ns
t_{OHA}	Output Hold from Address Change	3		3		5		5		5		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		12		15		20		25		35	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		12		10		10		12		15	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0		3		3		3		3		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z		7		8		8		10		12	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[7]	3		3		5		5		5		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[7, 8]		7		8		8		10		15	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		0		0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		12		15		20		20		20	ns
WRITE CYCLE[9]												
t_{WC}	Write Cycle Time	12		15		20		20		25		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	8		12		15		20		25		ns
t_{AW}	Address Set-Up to Write End	8		12		15		20		25		ns
t_{HA}	Address Hold from Write End	0		0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	8		12		15		15		20		ns
t_{SD}	Data Set-Up to Write End	6		10		10		10		15		ns
t_{HD}	Data Hold from Write End	0		0		0		0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[7] (7C162)	3		5		5		5		5		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[7, 8] (7C162)		6		7		7		7		10	ns
t_{AWE}	$\overline{WE}$ LOW to Data Valid (7C161)		12		15		20		25		30	ns
t_{ADV}	Data Valid to Output Valid (7C161)		12		15		20		20		30	ns
t_{DCE}	$\overline{CE}$ LOW to Data Valid		12		15		20		25		35	ns

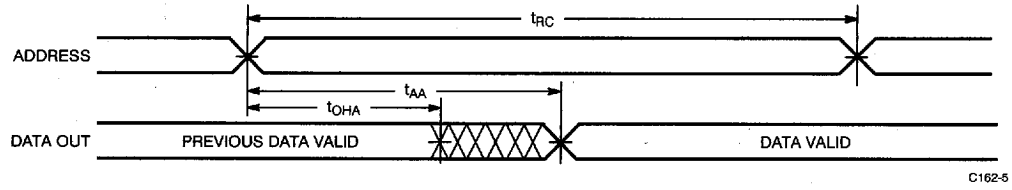
Shaded areas indicate preliminary information.

Notes:

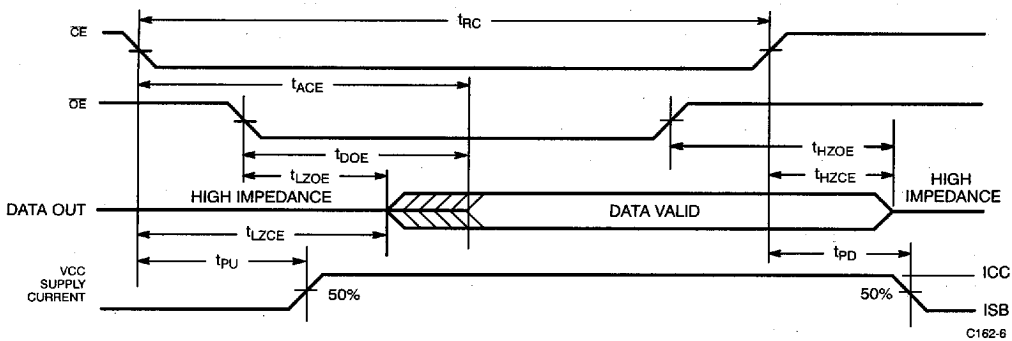
5. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
6. Both $\overline{CE}_1$ and $\overline{CE}_2$ are represented by $\overline{CE}$ in the Switching Characteristics and Waveforms sections.
7. At any given temperature and voltage condition, t_{HZ} is less than t_{LZ} for any given device.
8. t_{HZCE} and t_{HZWE} are specified with $C_L = 5$ pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
9. The internal write time of the memory is defined by the overlap of $\overline{CE}_1$ LOW, $\overline{CE}_2$ LOW, and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

Switching Waveforms[8]

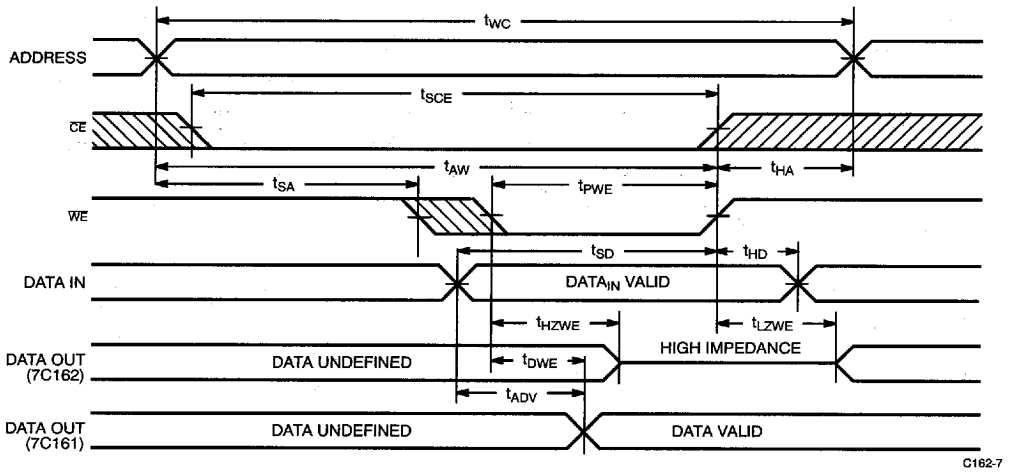
Read Cycle No. 1[10, 11]



Read Cycle No. 2[10, 12]



Write Cycle No. 1 ($\overline{WE}$ Controlled)[9]

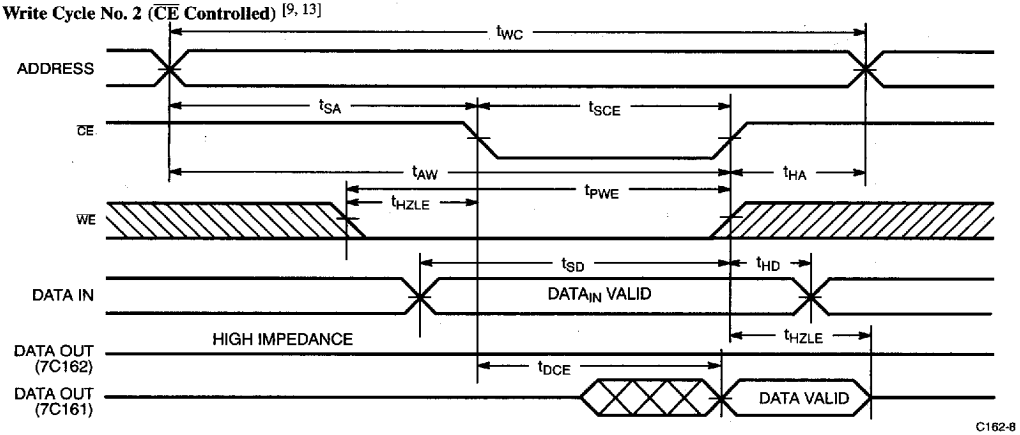


Notes:

10. $\overline{WE}$ is HIGH for read cycle.
11. Device is continuously selected, $\overline{CE}_1$, $\overline{CE}_2$ = V_{IL}.
12. Address valid prior to or coincident with $\overline{CE}_1$, $\overline{CE}_2$ transition LOW.

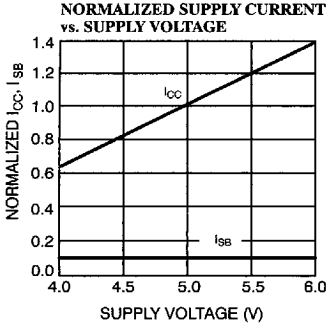
Switching Waveforms[8] (continued)

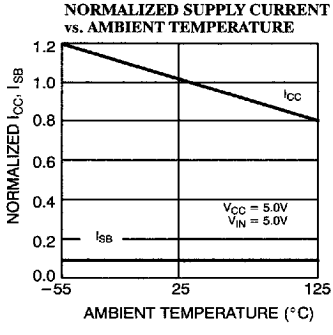
Write Cycle No. 2 ($\overline{CE}$ Controlled) [9, 13]

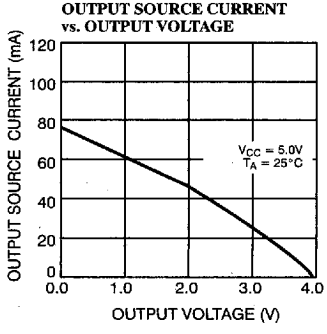


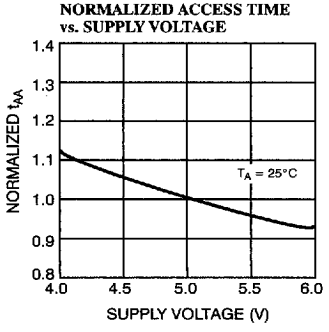
Note:
13. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state (7C162 only).

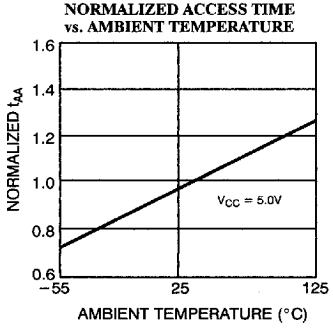
Typical DC and AC Characteristics

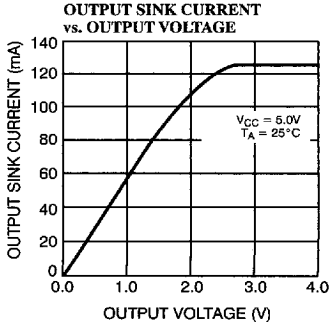




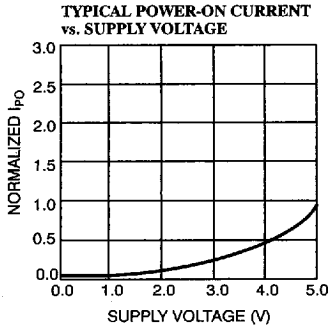


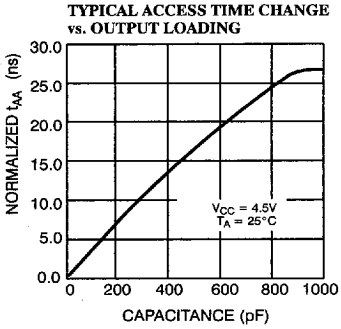


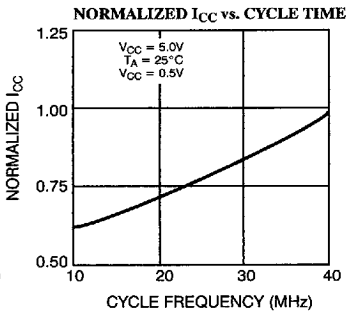




Typical DC and AC Characteristics (continued)







Address Designators

Address Name	Address Function	Pin Number
A5	X3	1
A6	X4	2
A7	X5	3
A8	X6	4
A9	X7	5
A10	Y0	6
A11	Y1	7
A12	Y5	8
A13	Y4	9
A0	Y3	23
A1	Y2	24
A2	X0	25
A3	X1	26
A4	X2	27

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C161–12PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C161–12VC	V21	28-Lead Molded SOJ	
15	CY7C161–15PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C161–15VC	V21	28-Lead Molded SOJ	
20	CY7C161–20PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C161–20VC	V21	28-Lead Molded SOJ	
25	CY7C161–25PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C161–25VC	V21	28-Lead Molded SOJ	
35	CY7C161–35PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C161–35VC	V21	28-Lead Molded SOJ	

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C162–12PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C162–12VC	V21	28-Lead Molded SOJ	
15	CY7C162–15PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C162–15VC	V21	28-Lead Molded SOJ	
20	CY7C162–20PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C162–20VC	V21	28-Lead Molded SOJ	
25	CY7C162–25PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C162–25VC	V21	28-Lead Molded SOJ	
35	CY7C162–35PC	P21	28-Lead (300-Mil) Molded DIP	Commercial
	CY7C162–35VC	V21	28-Lead Molded SOJ	

Shaded areas indicate preliminary information.

Document #: 38–00029–I